



Features

- Uses CRM(CQ) advanced Trench MOS technology
- Extremely low on-resistance RDS(on)
- Excellent QgxRDS(on) product(FOM)
- Qualified according to JEDEC criteria

Applications

- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

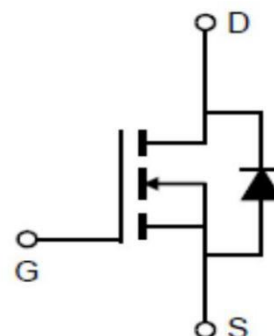
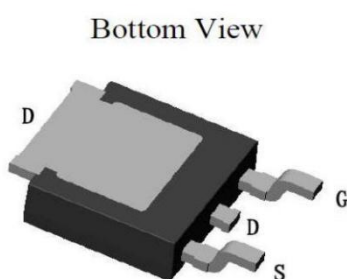
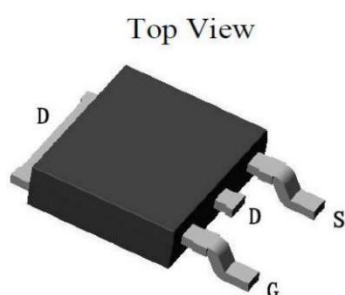
Product Summary

Vds	40V
ID	80A
RDS(ON) typ(at VGS = 10V)	6mΩ
RDS(ON) typ(at VGS = 4.5V)	8mΩ

100% DVDS Tested

100% Avalanche Tested

TO-252



Absolute Maximum Ratings TA=25°C unless otherwise noted

Parameter	Symbol	P-Channel	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	80	A
Drain Current-Continuous(T=100°C)	I _D (100°C)	61	A
Pulsed drain current (TC = 25°C, tp limited by Tjmax)	I _D pulse	320	A
Avalanche energy, single pulse (L=0.3mH, Rg=25Ω)	EAS	145	mJ
Power dissipation (TC = 25°C)	P _{tot}	81	W
Operating junction and storage temperature	T _j , T _{stg}	-55 To 150	°C

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R _{thJC}	12	°C/W
Thermal resistance, junction – ambient(min. footprint)	R _{thJA}	70	